NBA3N011S

3.3 V Automotive Grade LVDS Driver

Description

The NBA3N011S is a Low Voltage Differential Signaling (LVDS) driver for low power and high data rate applications. The device accepts LVCMOS/TTL input and translates it to LVDS and is designed to support data rates higher than 400 Mbps (200 MHz).

The driver provides low EMI with a typical output swing of 350 mV. The device can be paired with its companion single line receiver NBA3N012C or with any other LVDS receiver for high speed LVDS interface.

The LVDS output is designed as a 3.5 mA (typical) current mode driver allowing low power dissipation even at the high frequency.

NBA3N011S is offered in a 5 lead SOT23 package, shipping in 3000 pcs tape & reel.

Features

- Compatible with TIA/EIA–644A Standard
- Automotive Grade AECQ–100 Grade 1
- > 400 Mbps (200 MHz) Data Rate
- Operating Range: $V_{DD} = 3.3 \text{ V} \pm 0.3 \text{ V}$
- Maximum 700 ps Differential Skew
- Maximum Propagation Delay of 1.5 ns
- Low Power Dissipation (Typical 23 mW @ 3.3 V)
- SOT23-5 Lead Package with Pinout optimized for easy PCB Layout
- ±350 mV Differential Signaling
- Power Off Protection (Outputs in Tri-state)
- Temperature Operating Range –40°C to +125°C
- These are Pb–Free Devices

Typical Applications:

- Automotive: Head Lamp Lighting for Cars
- Telecom: Wireless, Microwave and Optical

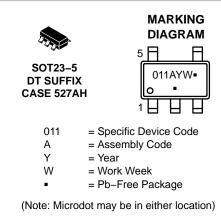
Table 1. PIN DESCRIPTION

Pin Number	Pin Name	I/O Type	Description
1	V _{DD}		Power Supply Pin
2	GND		Ground Pin
3	Q	Output	Inverting Output Pin
4	Q	Output	Non–Inverting Output
5	IN	Input	Input Pin

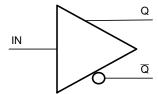


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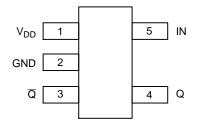
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PINOUT DIAGRAM



ORDERING INFORMATION

Device	Package	Shipping [†]
NBA3N011SSNT1G	SOT23–5 (Pb–Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

Table 2. ATTRIBUTES (Note 1)

	Value			
ESD Protection	ESD Protection Human Body Model (JEDEC Standard 22, Method A114–E) All Pins			
	Charge Device Model (JEDEC Standard 22, Method C101D) All Pins			
Moisture Sensitivity (Note 1)			Level 1	
Flammability Rating	Oxygen Index: 28 to 34		UL 94 Code V–0 A 0.125 in 28 to 34	

1. For additional information, see Application Note AND8003/D

Table 3. MAXIMUM RATINGS

Symbol	Parameter	Rating	Unit
V _{DD}	Supply voltage	$-0.30 \le V_{DD} \le 4.0$	V
V _{IN}	Input Voltage (IN) LVCMOS	–0.30 to (V _{DD} + 0.30)	V
V _Q	Output Voltage (Q/Q) LVDS	-0.30 to +3.90	V
I _{OS}	Output Short Circuit Current LVDS	24	mA
Tj	Maximum Junction Temperature	135	°C
Tstg	Storage Temperature Range	-65 to +150	°C
θ_{JC}	Thermal resistance (Junction-to-Case) - (Note 3)	107	°C/W
θ_{JA}	Thermal resistance (Junction-to-Ambient) - (Note 3)	138.5	°C/W
T _{sol}	Lead Temperature Soldering (4 Seconds) – SOLDERRM/D	260	°C
PD	Package Power Dissipation @ 25°C – Derating of 7.22 mW/°C above 25°C	794	mW

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
The maximum ratings applied are individual stress limit values and not valid simultaneously.
JEDEC standard multilayer board –2S2P (2 signal 2 power)

Table 4. DC CHARACTERISTICS V_{DD} = 3.3 V \pm 0.3 V, GND = 0 V, T_A -40°C to +125°C

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
I _{DD}	Power Supply Current	No–Load (Pin: V_{DD} ; $V_{IN} = V_{DD}$ or GND)		5	8	mA
		RL = 100 Ω (Pin: V _{DD} ; V _{IN} = V _{DD} or GND)		7	10	mA
V _{IH}	Input High Voltage	Pin: IN	2.0		V _{DD}	V
VIL	Input Low Voltage	Pin: IN	GND		0.8	V
I _{IH}	Input High Current	Pin: IN; V_{IN} = 3.3 V or 2.4 V		±2	±10	μΑ
I _{IL}	Input Low Current	Pin: IN; V_{IN} = GND or 0.5 V		±1	±10	μΑ
V _{CL}	Input Clamp Voltage	$I_{CL} = -18 \text{ mA}$	-1.5	-0.6		V
C _{IN}	Input Capacitance			3		pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
V _{OD}	Differential Output Voltage	$R_L = 100 \Omega$, Figures 1 & 2	250	350	450	mV
$\Delta V_{OD} $	Change in Differential Output Voltage magnitude			3	35	mV
V _{OS}	Offset Voltage	R_L = 100 Ω, Figure 1	1.125	1.220	1.375	V
ΔV_{OS}	Change in Offset Voltage magnitude		0	1	50	mV
I _{OFF}	Leakage Current – Power–off	V_Q = 3.6 V or GND, V_{DD} = 0 V		±1	±10	μΑ
I _{OSD}	Differential Short Circuit Output Current (Note 4)	V _{OD} = 0 V		-5	-12	mA
I _{OS}	Output Short Circuit Current (Note 4)	V_Q and $V_{\overline{Q}} = 0 V$		-6	-24	mA
C _{OUT}	Output Capacitance			3		pF

Table 5. ELECTRICAL CHARACTERISTICS V_{DD} = 3.3 V \pm 0.3 V, GND = 0 V, T_A -40°C to +125°C, Pin: Q/Q

4. - minus sign indicated only direction. Current into the device is defined as positive. I_{OS}/I_{OSD} is specified as magnitude only.

Table 6. SWITCHING CHARACTERISTICS

 $V_{DD} = 3.3 \text{ V} \pm 0.3 \text{ V}, \text{ GND} = 0 \text{ V}, \text{ } \text{T}_{\text{A}} - 40^{\circ}\text{C} \text{ to } + 125^{\circ}\text{C}, \text{ } \text{F} = 1 \text{ MHz}, \text{ } \text{Z}_{\text{O}} = 50 \text{ } \Omega, \text{ } \text{t}_{\text{f}}, \text{ } \text{t}_{\text{f}} \leq 1 \text{ ns} \text{ (10\% to } 90\%) - \text{ (Note 5)} \text$

Symbol	Parameters	Min	Тур	Max	Unit
t _{pHLD}	High to Low Differential Propagation Delay	0.3	1.0	1.5	ns
t _{pLHD}	Low to High Differential Propagation Delay	0.3	1.1	1.5	ns
t _r	Rise Time – Transition Low to High	0.2	0.5	1.0	ns
t _f	Fall Time – Transition High to Low	0.2	0.5	1.0	ns
t _{SKD(P)}	Differential Pulse Skew t _{pHLD} - t _{pLHD} (Note 6)	0	0.1	0.7	ns
t _{SKD(PP)1}	Differential Part to Part Skew – (Note 7)	0	0.2	1.0	ns
t _{SKD(PP)2}	Differential Part to Part Skew – (Note 8)	0	0.4	1.2	ns
f _{MAX}	Maximum Operating Frequency – (Note 9)		250		MHz

5. Test Conditions for the above – R_L = 100 Ω , C_L = 15 pF (includes Load & Jig Capacitance), Figures 3 and 4

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions

[t_{PHLD} - t_{PLHD}], is the magnitude difference in differential propagation delay time between the positive going edge and the negative going edge of the same channel.

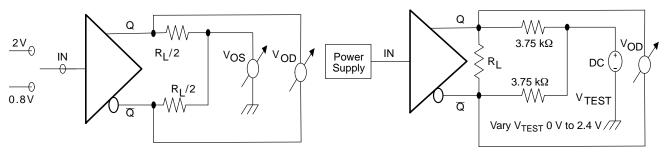
Differential Part to Part Skew, is defined as the difference between the minimum and maximum specified differential propagation delays. This specification applies to devices at the same V_{DD} and within 5°C of each other within the operating temperature range.
Part to part skew, is the differential channel to channel skew of any event between devices. This specification applies to devices over

 Part to part skew, is the differential channel to channel skew of any event between devices. This specification applies to devices over recommended operating temperature and voltage ranges, and across process distribution. t_{SKD2} is defined as |Max – Min| differential propagation delay.

9. f_{MAX} Input Conditions: t_r = t_f < 1 ns (0% to 100%), Duty Cycle 50%, 0 V to 3 V. f_{MAX} Output Conditions: V_{OD} > 250 mV, Duty Cycle = 45%/55%

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PARAMETER MEASUREMENT:



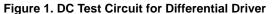


Figure 2. Full Load DC Test Circuit for Differential Driver

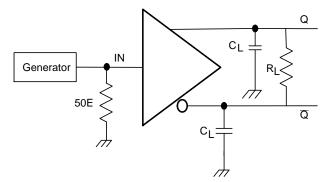


Figure 3. Propagation Delay & Transition Time Test Circuit for Differential Driver

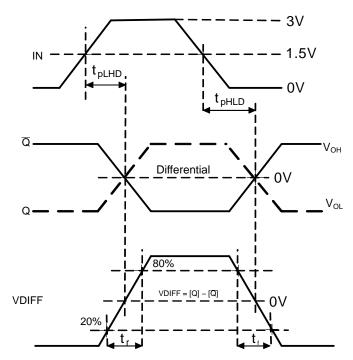
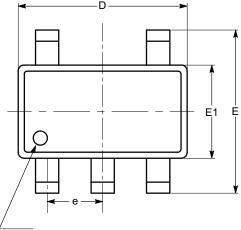


Figure 4. Propagation Delay & Transition Time Waveforms for Differential Driver

PACKAGE DIMENSIONS

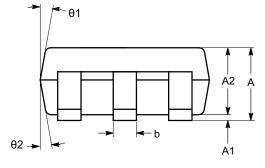
SOT-23, 5 Lead CASE 527AH ISSUE O



PIN #1 IDENTIFICATION



SYMBOL	MIN	NOM	МАХ	
А	0.90		1.45	
A1	0.00		0.15	
A2	0.90	1.15	1.30	
b	0.30		0.50	
с	0.08		0.22	
D	2.90 BSC			
E	2.80 BSC			
E1	1.60 BSC			
е	0.95 BSC			
L	0.30 0.45 0.60			
L1	0.60 REF			
L2	0.25 REF			
θ	0° 4° 8°			
θ1	5°	10°	15°	
θ2	5°	10°	15°	



SIDE VIEW

Notes:

(1) All dimensions in millimeters. Angles in degrees.

(2) Complies with JEDEC standard MO-178.

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